RELIABILITY REPORT

FOR

DG413DY+
(DG411/DG412/DG413)

PLASTIC ENCAPSULATED DEVICES

April 9, 2009

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.

SUNNYVALE, CA 94086

Approved by
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Quality Assurance
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Conclusion

The DG413DY+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim"s continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim"s quality and reliability standards.

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I. Device Description

A. General

Maxim's redesigned DG411/DG412/DG413 analog switches now feature low on-resistance matching between switches (3 max) and guaranteed on-resistance flatness over the signal range (4 max). These low on-resistance switches conduct equally well in either direction. They guarantee low charge injection, low power consumption, and an ESD tolerance of 2000V minimum per Method 3015.7. The new design offers lower off-leakage current over temperature (less than 5nA at +85°C). The DG411/DG412/DG413 are quad, single-pole/single-throw (SPST) analog switches. The DG411 is normally closed (NC), and the DG412 is normally open (NO). The DG413 has two NC switches and two NO switches. Switching times are less than 150ns max for tON and less than 100ns max for tOFF. These devices operate from a single +10V to +30V supply, or bipolar ±4.5V to ±20V supplies. Maxim's improved DG411/DG412/DG413 are fabricated with a 44V silicon-gate process.

II. Manufacturing Information

A. Description/Function:	Improved, Quad, SPST Analog Switches
B. Process:	S5
C. Number of Device Transistors:	
D. Fabrication Location:	Oregon
E. Assembly Location:	ATP Philippines, UTL Thailand, Carsem Malaysia
F. Date of Initial Production:	April 27, 2002

III. Packaging Information

A. Package Type:	16-pin SOIC (N)
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive Epoxy
E. Bondwire:	Gold (1.3 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-0301-0596
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	115°C/W
K. Single Layer Theta Jc:	32°C/W
L. Multi Layer Theta Ja:	82.2°C/W
M. Multi Layer Theta Jc:	32°C/W

IV. Die Information

A. Dimensions:	80 X 97 mils
B. Passivation:	Si_3N_4/SiO_2 (Silicon nitride/ Silicon dioxide
C. Interconnect:	Aluminum/Si (Si = 1%)
D. Backside Metallization:	None
E. Minimum Metal Width:	5.0 microns (as drawn)
F. Minimum Metal Spacing:	5.0 microns (as drawn)
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO_2
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

A. Quality Assurance Contacts:	Ken Wendel (Director, Reliability Engineering) Bryan Preeshl (Managing Director of QA)
B. Outgoing Inspection Level:	0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects.
C. Observed Outgoing Defect Rate:	< 50 ppm
D. Sampling Plan:	Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 80 \times 2} \quad \text{(Chi square value for MTTF upper limit)}$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$\lambda = 13.4 \times 10^{-9}$

λ = 13.4 F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly 1000 hour life test monitors on its processes. This data is published in the Product Reliability Report found at http://www.maxim-ic.com/. Current monitor data for the S5HV Process results in a FIT Rate of 1.38 @ 25C and 16.71 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

C. E.S.D. and Latch-Up Testing

The AG38-2 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2000 per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-250 mA.

Table 1

Reliability Evaluation Test Results

DG413DY+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test (Note 1)				
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	80	0
Moisture Testing (Note 2)				
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	77	0
Mechanical Stress (Note 2)				
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0

Note 1: Life Test Data may represent plastic DIP qualification lots.
Note 2: Generic Package/Process data